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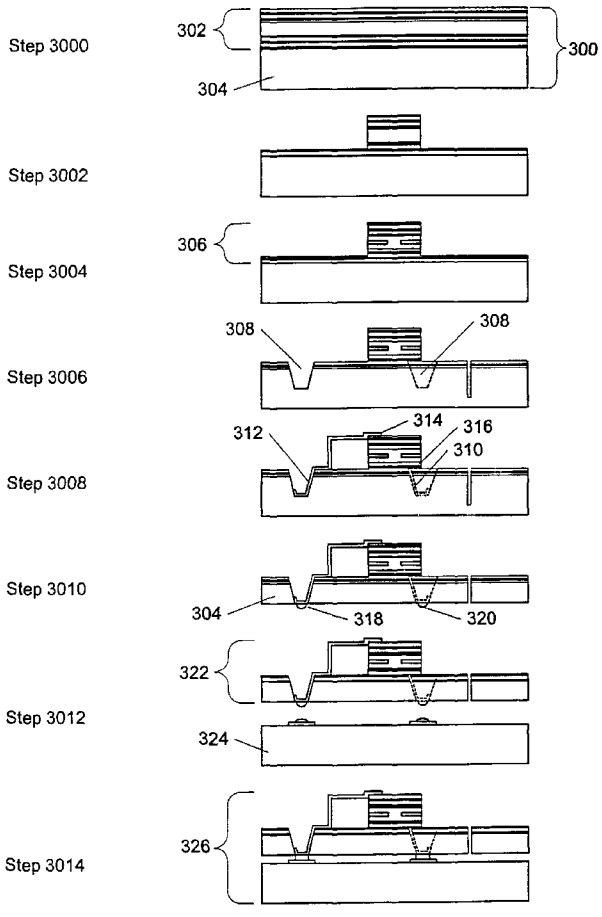
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(54) Title: TOPSIDE ACTIVE OPTICAL DEVICE APPARATUS AND METHOD



(57) Abstract: A method of integrating a topside optical device, having electrical contacts on a top side, with an electronic chip (324) having electrical contacts on a connection side, involves creating a trench (308), defined by a wall, from the top side of a wafer containing the topside optical device into a substrate (304) of the wafer, making a portion of the wall conductive by applying a conductive material to the portion; and thinning the substrate to expose the conductive material.

WO 03/003423 A1

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